

74HC157-Q100; 74HCT157-Q100

Quad 2-input multiplexer

Rev. 2 — 21 January 2015

Product data sheet

1. General description

The 74HC157-Q100; 74HCT157-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL. It is specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT157-Q100 are quad 2-input multiplexers which select 4 bits of data from two sources under the control of a common data select input (S). The enable input ($\overline{E}$) is active LOW. When $\overline{E}$ is HIGH, all of the outputs (1Y to 4Y) are forced LOW regardless of all other input conditions.

Moving the data from two groups of registers to four common output buses is a common use of the 74HC/HCT157-Q100. The state of the common data select input (S) determines the particular register from which the data comes. It can also be used as function generator. The device is useful for implementing highly irregular logic by generating any four of the 16 different functions of two variables with one variable common. The 74HC/HCT157-Q100 is logic implementation of a 4-pole, 2-position switch, where the position of the switch is determined by the logic levels applied to S.

The logic equations are:

$$1Y = \overline{E} \times (1I1 \times S + 1I0 \times \overline{S})$$

$$2Y = \overline{E} \times (2I1 \times S + 2I0 \times \overline{S})$$

$$3Y = \overline{E} \times (3I1 \times S + 3I0 \times \overline{S})$$

$$4Y = \overline{E} \times (4I1 \times S + 4I0 \times \overline{S})$$

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Low-power dissipation
- Non-inverting data path
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

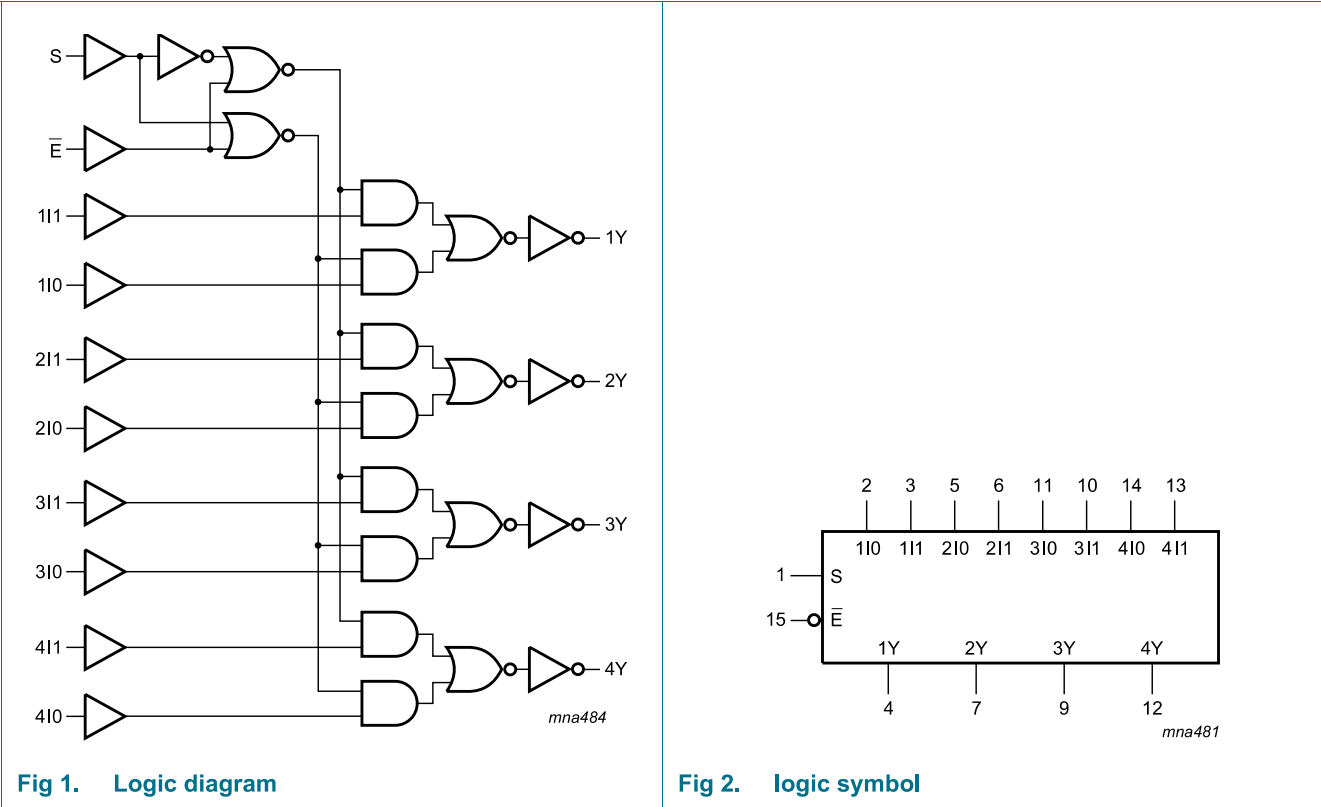


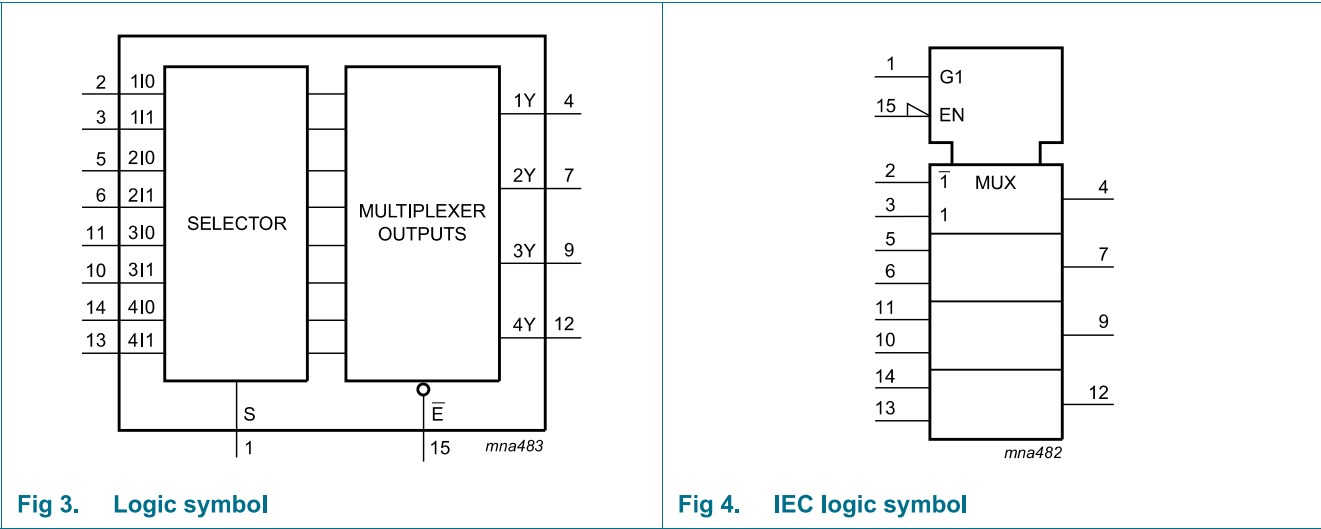
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC157D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT157D-Q100				
74HC157PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT157PW-Q100				
74HC157BQ-Q100	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT157BQ-Q100				

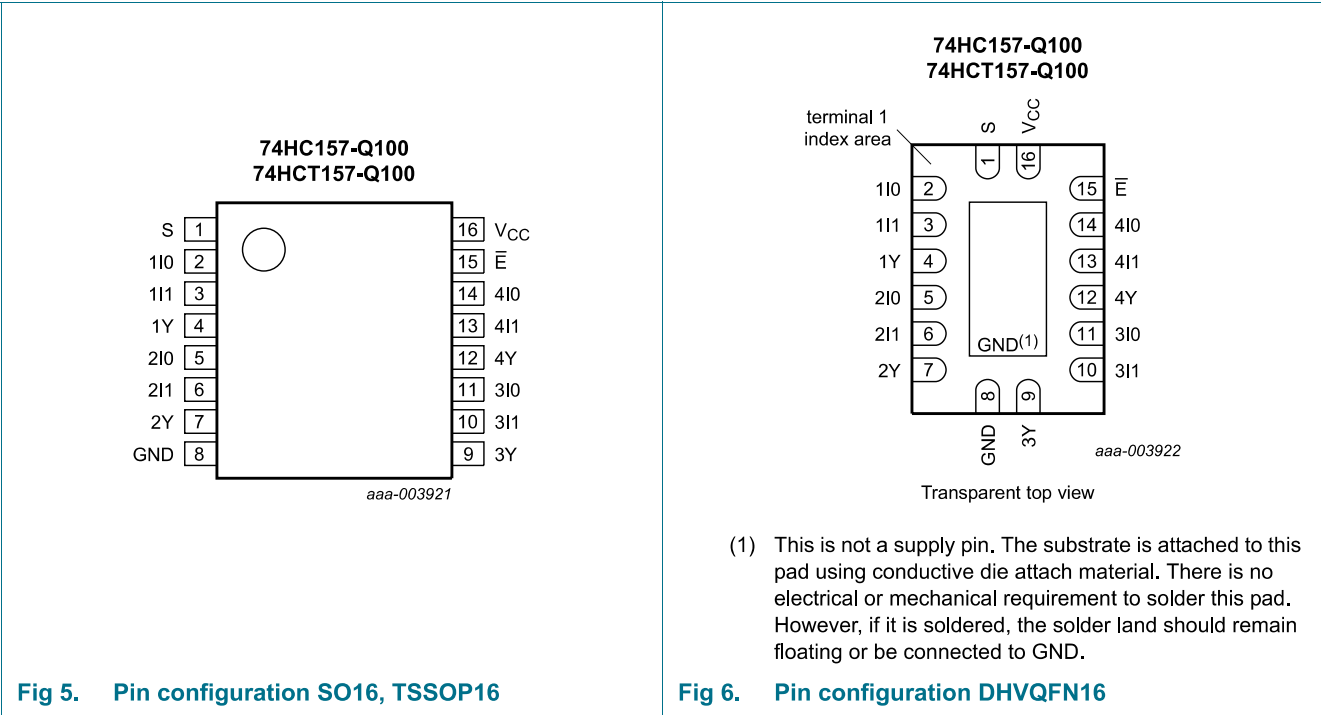
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
S	1	common data select input
1I0 to 4I0	2, 5, 11, 14	data inputs from source 0
1I1 to 4I1	3, 6, 10, 13	data inputs from source 1
1Y to 4Y	4, 7, 9, 12	multiplexer outputs
GND	8	ground (0 V)
$\overline{E}$	15	enable input (active LOW)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Input				Output
$\overline{E}$	S	nI0	nI1	nY
H	X	X	X	L
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	-	±25	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-	-50	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
		SO16 package ^[1]	-	500	mW
		TSSOP16 package ^[2]	-	500	mW
		DHVQFN16 package ^[3]	-	500	mW

[1] P_{tot} derates linearly with 8 mW/K above 70 °C.

[2] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[3] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC157-Q100			74HCT157-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = −40 °C to +85 °C		T _{amb} = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC157-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = −4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	I _O = −5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
		V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
		V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = –40 °C to +85 °C		T _{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _I	input capacitance		-	3.5	-					pF
74HCT157-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		per input pin; nI0, nI1 inputs	-	100	360	-	450	-	490	µA
		per input pin; $\overline{E}$ input	-	60	216	-	270	-	294	µA
		per input pin; S input	-	100	360	-	450	-	490	µA
C _I	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 9](#).

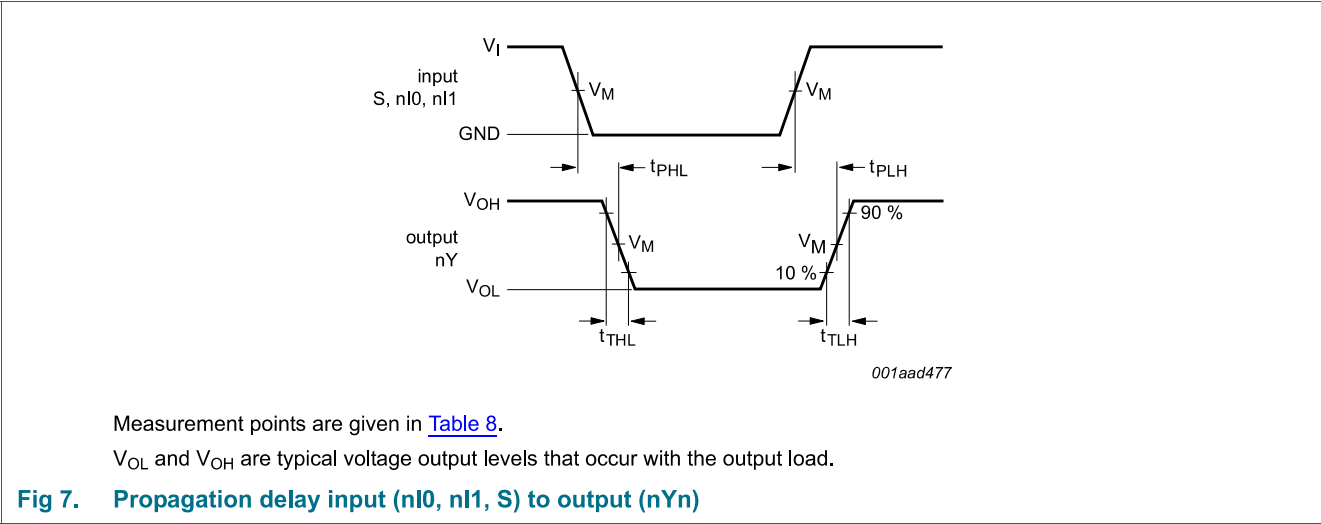
Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = −40 °C to +85 °C		T _{amb} = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC157-Q100										
t _{pd}	propagation delay	nI0, nI1 to nY; see Figure 7 ^[1]								
		V _{CC} = 2.0 V	-	36	125	-	155	-	190	ns
		V _{CC} = 4.5 V	-	13	25	-	31	-	38	ns
		V _{CC} = 5 V; C _L = 15 pF	-	11	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	10	21	-	26	-	32	ns
		S to nY; see Figure 7 ^[1]								
		V _{CC} = 2.0 V	-	41	125	-	155	-	190	ns
		V _{CC} = 4.5 V	-	15	25	-	31	-	38	ns
		V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	12	21	-	26	-	32	ns
		$\overline{E}$ to nY; see Figure 8 ^[1]								
		V _{CC} = 2.0 V	-	39	115	-	145	-	175	ns
		V _{CC} = 4.5 V	-	14	23	-	29	-	35	ns
		V _{CC} = 5 V; C _L = 15 pF	-	11	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	11	20	-	25	-	30	ns
t _t	transition time	nY; see Figure 7 ^[2]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC} ^[3]	-	70	-	-	-	-	-	pF
74HCT157-Q100										
t _{pd}	propagation delay	nI0, nI1 to nY; see Figure 7 ^[1]								
		V _{CC} = 4.5 V	-	16	27	-	34	-	41	ns
		V _{CC} = 5 V; C _L = 15 pF	-	13	-	-	-	-	-	ns
		S to nY; see Figure 7 ^[1]								
		V _{CC} = 4.5 V	-	22	37	-	46	-	56	ns
		V _{CC} = 5 V; C _L = 15 pF	-	19	-	-	-	-	-	ns
		$\overline{E}$ to nY; see Figure 8 ^[1]								
		V _{CC} = 4.5 V	-	15	26	-	33	-	39	ns
	V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns	

Table 7. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); $C_L = 50\text{ pF}$ unless otherwise specified; for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = –40 °C to +85 °C		T _{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _t	transition time	nY; see Figure 7 [2]								
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC} – 1.5 V [3]	-	70	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
 [2] t_t is the same as t_{THL} and t_{TLH}.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



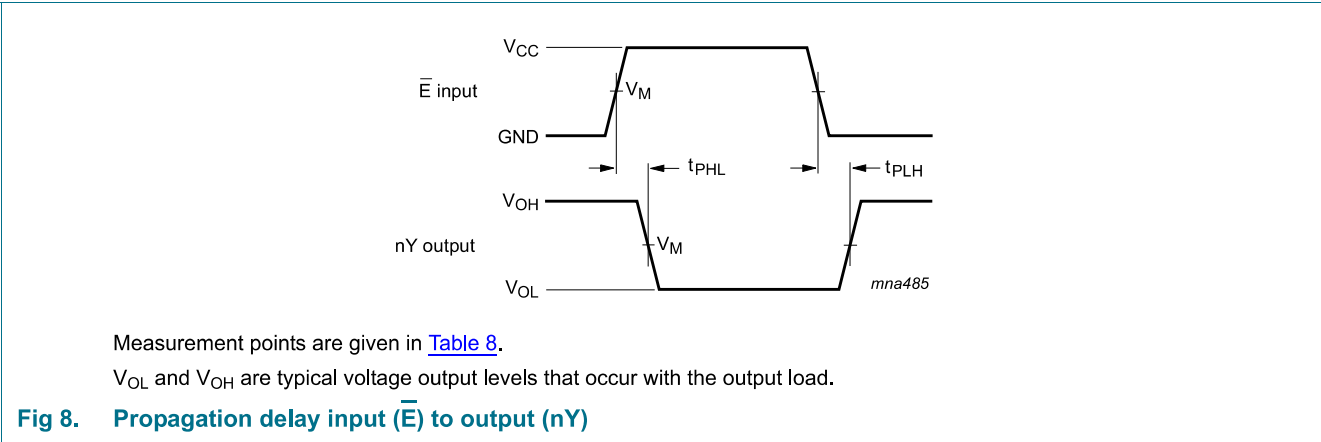
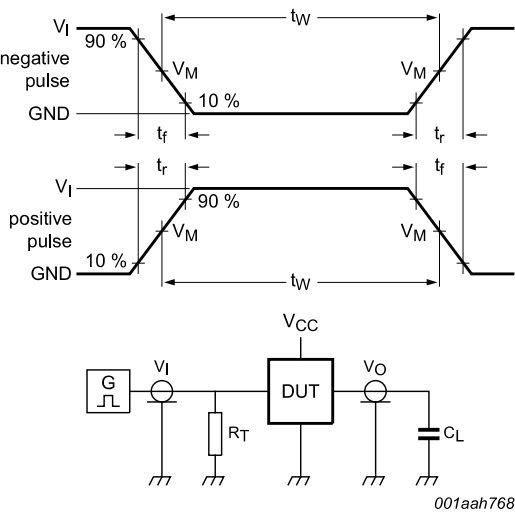


Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC157-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74HCT157-Q100	1.3 V	1.3 V



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 9. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74HC157-Q100	V_{CC}	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74HCT157-Q100	3.0 V	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

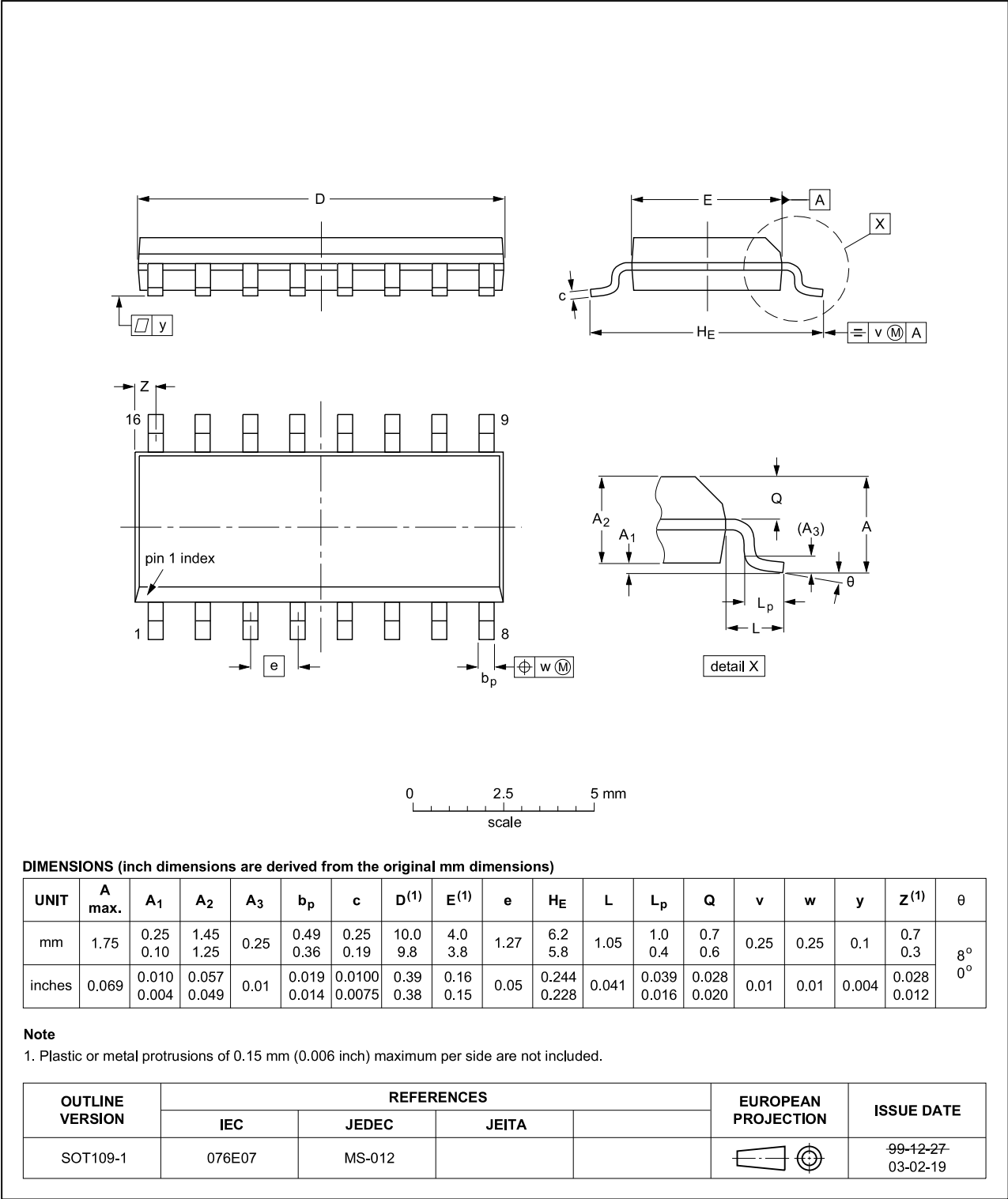


Fig 10. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

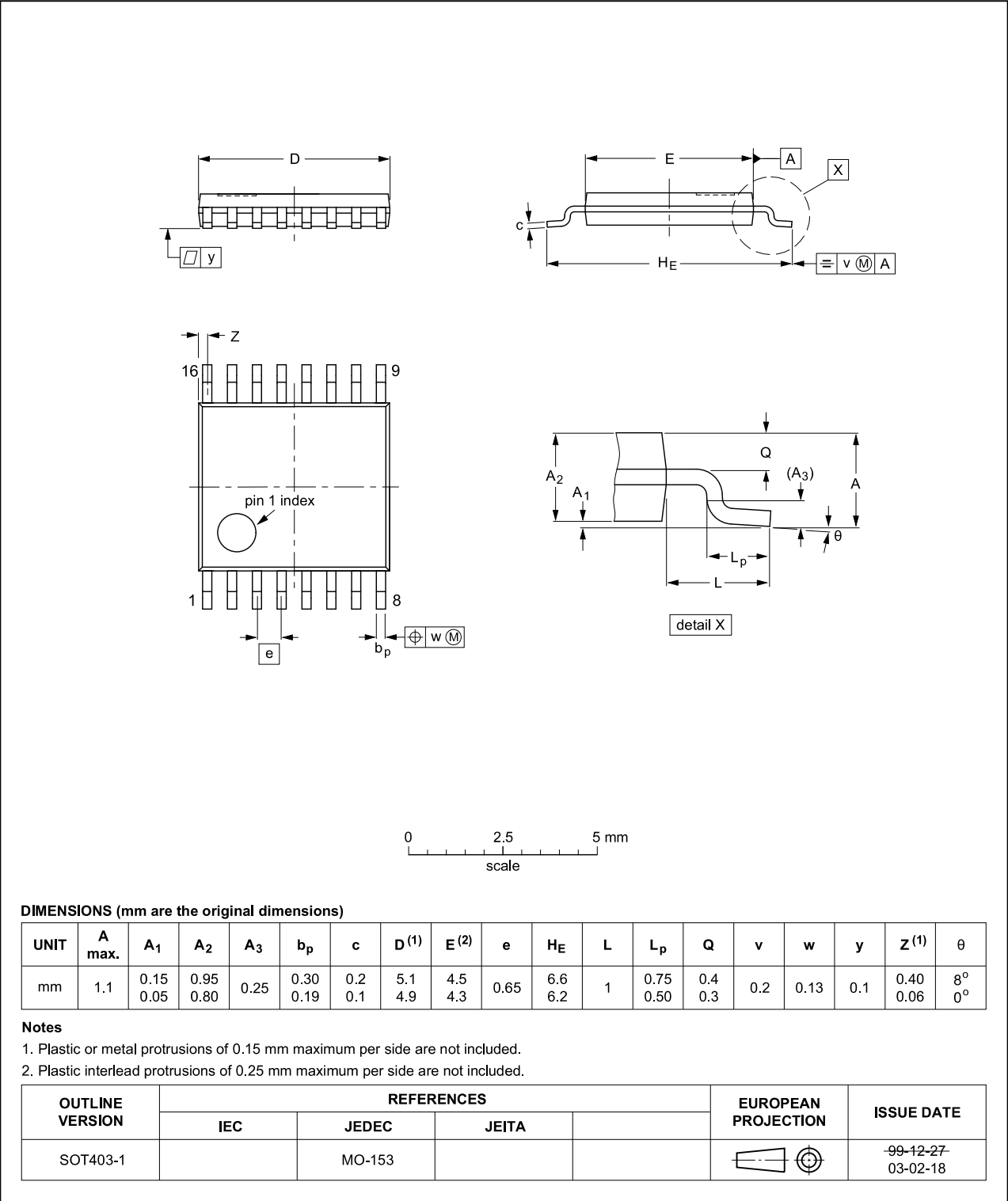


Fig 11. Package outline SOT403-1 (TSSOP16)